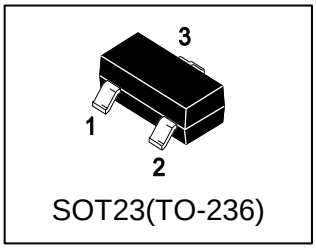
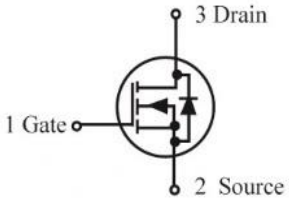
LBSS138LT1G
S-LBSS138LT1G

Power MOSFET
200 mAmps, 50 Volts N–Channel SOT-23



SOT23(TO-236)



1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low threshold voltage (VGS(th): 0.5V...1.5V) makes it ideal for low voltage applications.

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBSS138LT1G	J1	3000/Tape&Reel
LBSS138LT3G	J1	10000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25ºC)

Parameter	Symbol	Limits	Unit
Drain–Source Voltage	VDSS	50	Vdc
Gate–to–Source Voltage – Continuous	VGS	±20	Vdc
Drain Current – Continuous TA = 25°C – Pulsed (tp≤10μs)	 ID IDM	 200 800	mAdc

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR−5 Board (Note 1) @ TA = 25ºC Derate above 25ºC	PD	225 1.8	mW mW/ºC
Thermal Resistance, Junction–to–Ambient(Note 1)	RΘJA	556	ºC/W
Junction and Storage temperature	TJ,Tstg	−55~+150	° C
Maximum Lead Temperature for Solde Purposes, for 10 seconds	TL	260	ºC

1. FR–5 = 1.0×0.75×0.062 in.

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5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain–Source Breakdown Voltage (VGS = 0, ID = 250μAdc)	VBRDSS	50	-	-	Vdc
Zero Gate Voltage Drain Current (VGS = 0, VDS = 25 Vdc) (VGS = 0, VDS = 50 Vdc)	IDSS	- -	- -	0.1 0.5	μAdc
Gate–Body Leakage Current, Forward (VGS = 20 Vdc)	IGSSF	-	-	0.1	μAdc
Gate–Body Leakage Current, Reverse (VGS = - 20 Vdc)	IGSSR	-	-	-0.1	μAdc

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage (VDS = VGS, ID = 1.0mAdc)	VGS(th)	0.5	-	1.5	Vdc
Static Drain–Source On–State Resistance (VGS = 2.75 Vdc, ID < 200 mAdc, TA = –40°C to +85°C) (VGS = 5.0 Vdc, ID = 200 mAdc)	RDS(on)	- -	5.6 -	10 3.5	Ohms
Forward Transconductance (VDS = 25 Vdc, ID = 200 mAdc, f = 1.0 kHz)	gfs	100	-	-	mS

DYNAMIC CHARACTERISTICS

Input Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Ciss	-	40	50	pF
Output Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Coss	-	12	25	pF
Reverse Transfer Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Ciss	-	3.5	5.0	pF

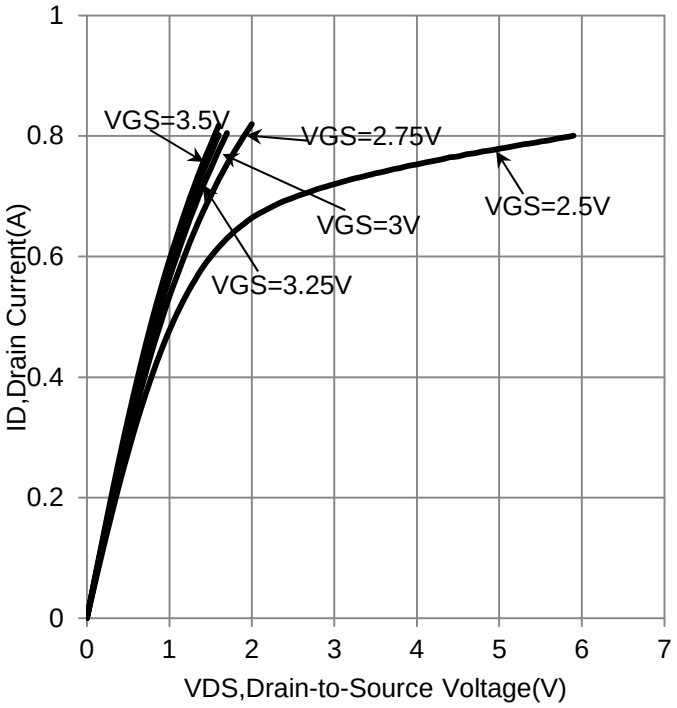
SWITCHING CHARACTERISTICS

Turn-On Delay Time	(VDD = 30 Vdc , ID =200 mAdc)	td(on)	-	-	20	ns
Turn-Off Delay Time		td(off)	-	-	20	

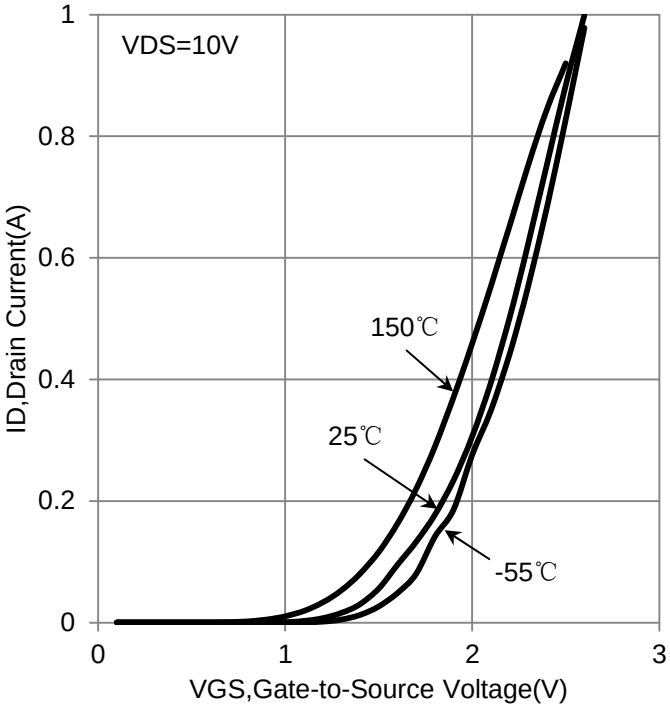
2.Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2.0%.

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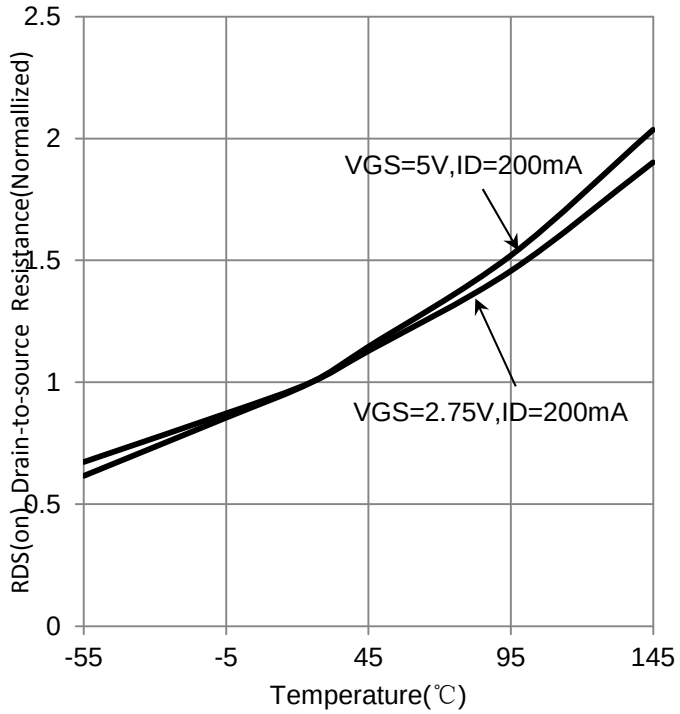
6. ELECTRICAL CHARACTERISTICS CURVES



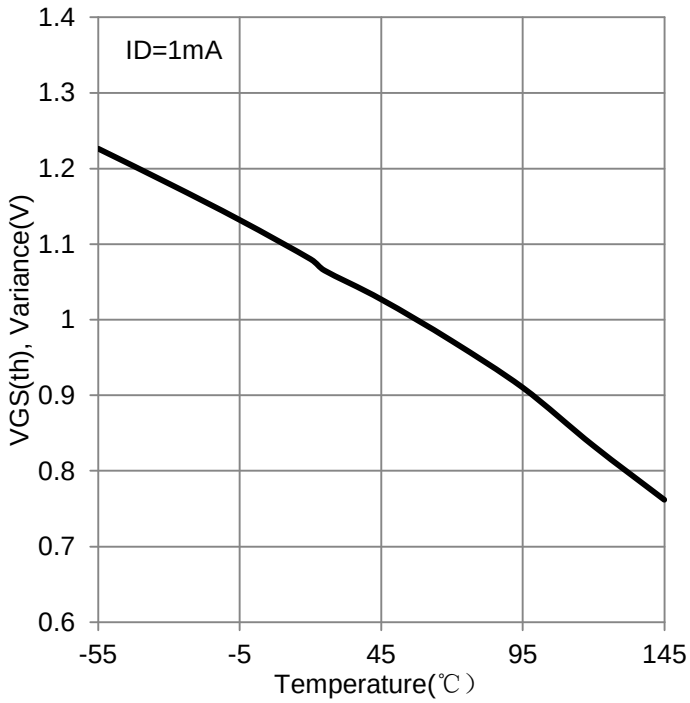
On-Region Characteristics



Transfer Characteristics



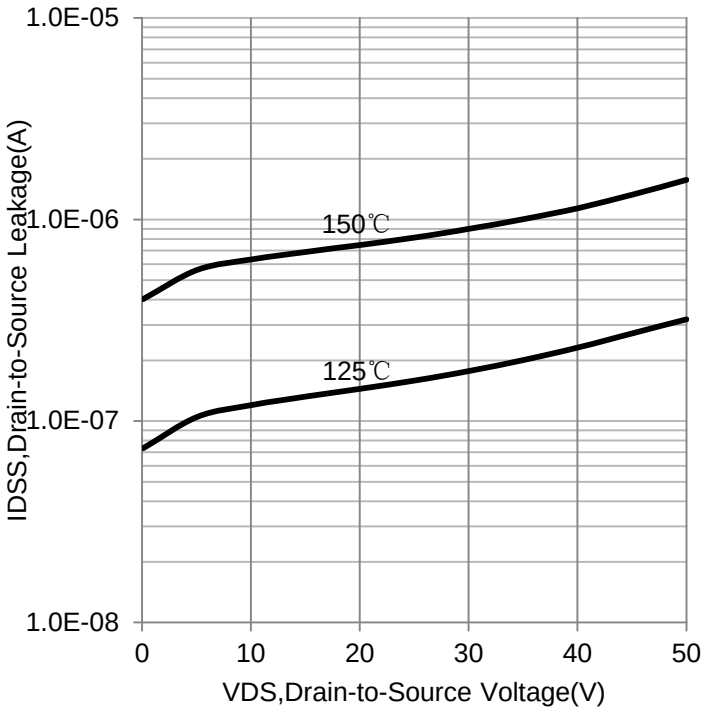
RDS(on) vs. Temperature



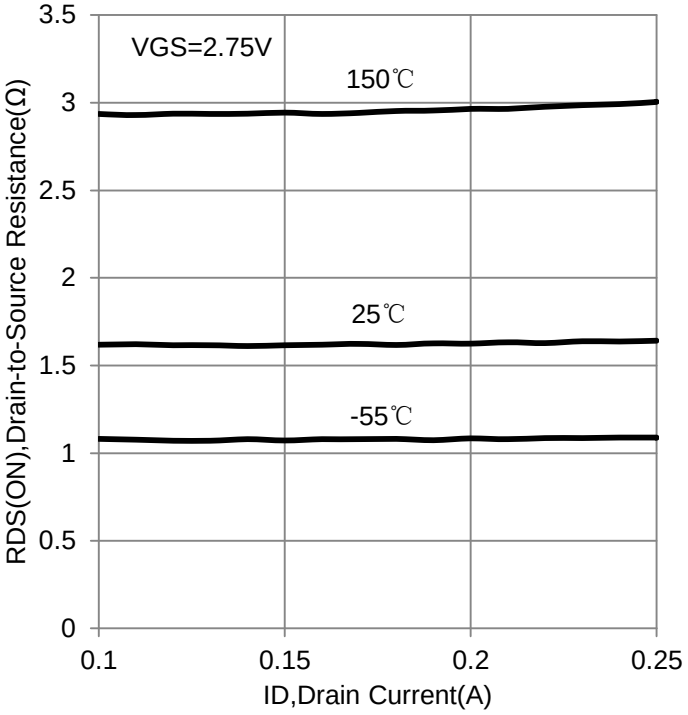
Threshold Voltage vs.Temperature

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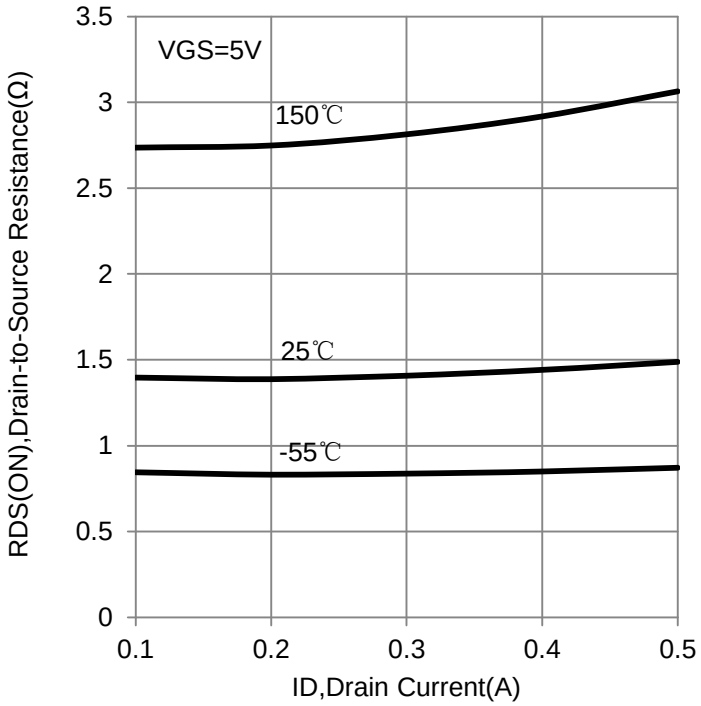
6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



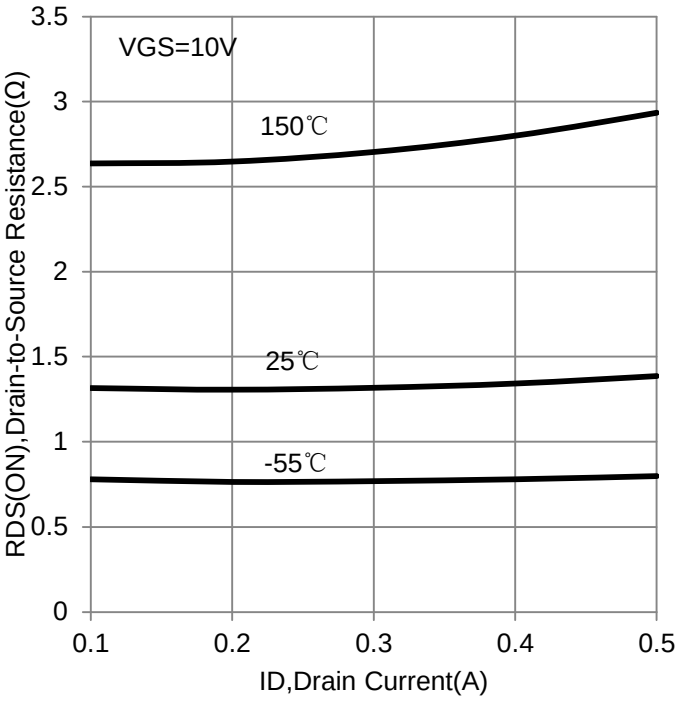
IDSS vs. VDS



RDS(on) vs. ID



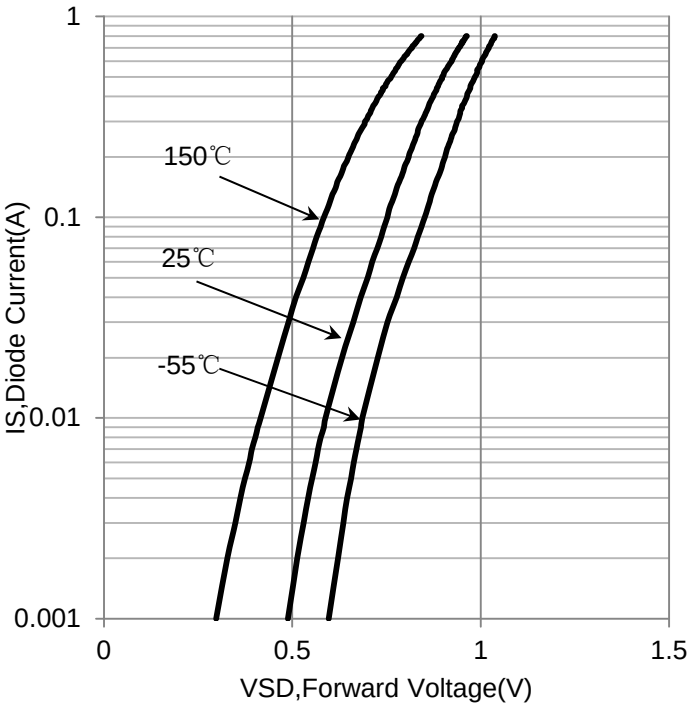
RDS(on) vs. ID



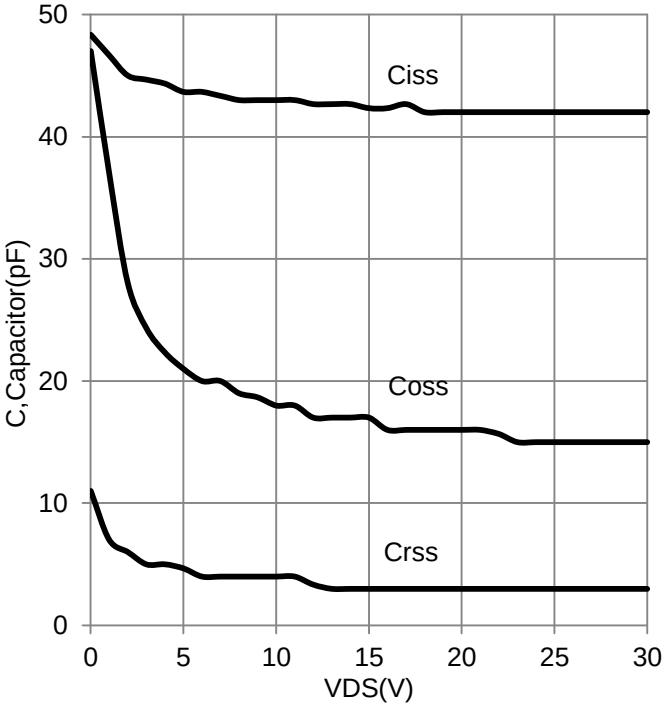
RDS(on) vs. ID

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6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



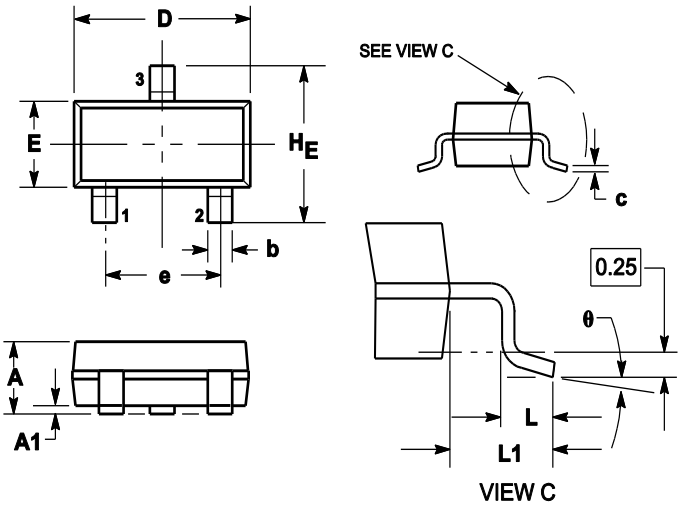
Body Diode Forward Voltage



Capacitor vs.VDS

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7.OUTLINE AND DIMENSIONS

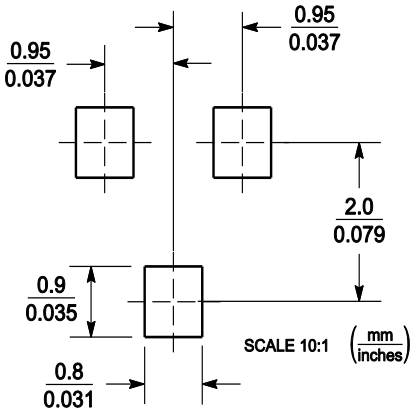


Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

8.SOLDERING FOOTPRINT



Shanghai Leiditech Electronic Co.,Ltd
Email: sale1@leiditech.com
Tel : +86- 021 50828806
Fax : +86- 021 50477059

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